

Title (en)

INSULATION TRENCH FOR AN INTEGRATED CIRCUIT AND METHOD FOR PRODUCTION THEREOF

Title (de)

ISOLATIONSGRABEN FUR EINE INTEGRIERTE SCHALTUNG UND VERFAHREN ZU DESSEN HERSTELLUNG

Title (fr)

TRANCHEE D'ISOLATION DESTINEE A UN CIRCUIT INTEGRE ET PROCEDE DE FABRICATION DE CETTE TRANCHEE

Publication

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Application

**EP 02799043 A 20021115**

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Abstract (en)

[origin: WO03046977A2] The invention relates to an insulation trench (1) for an integrated circuit, formed in a substrate (2) and filled with an insulation medium (7) with a low relative dielectric constant. On the upper face thereof, the insulation trench is sealed with a cover (12), such that the insulating medium (7) is completely encapsulated. The invention further relates to a bottle-shaped insulation trench and a method for production of an insulation trench.

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IPC 8 full level

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Citation (search report)

See references of WO 03046977A2

Citation (examination)

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